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EDUCATION

- Ph.D., Candidate, Electrical Engineering Sep. 2012 – Present
Korea Advanced Institute of Science and Technology (KAIST), Daejeon, South Korea
- M.S., Electrical Engineering Sep. 2010 – Aug. 2012
Korea Advanced Institute of Science and Technology (KAIST), Daejeon, South Korea
- B.S., Electrical Engineering Mar. 2006 – Aug. 2010
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Journals

1. "Triboelectric Nanogenerator Based on the Internal Motion of Powder with a Package Structure Design", Daewon Kim, Yura Oh, **Byeong-Woon Hwang**, Seung-Bae Jeon, Sang-Jae Park, and Yang-Kyu Choi, *ACS Nano*, (2015)
2. "Germanium Electron-Hole Bilayer Tunnel Field-Effect Transistors with a Symmetrically Arranged Double Gate", Woo Jin Jeong, Tae Kyun Kim, Jung Min Moon, Min Gyu Park, Young Gwang Yoon, **Byeong Woon Hwang**, Woo Young Choi, Mincheol Shin, and Seok-Hee Lee, *Semiconductor Science and Technology*, 30, 035021 (2015)
3. "Explicit Analytical Current-Voltage Model for Double-Gate Junctionless Transistors", **Byeong-Woon Hwang**, Ji-Woon Yang, and Seok-Hee Lee, *IEEE Transactions on Electron Devices*, 62 (1), 171-177 (2015)
4. "Origin of Device Performance Enhancement of Junctionless Accumulation-Mode (JAM) Bulk FinFETs with High- κ Gate Spacers", Ji Hun Choi, Tae Kyun Kim, Jung Min Moon, Young Gwang Yoon, **Byeong Woon Hwang**, Dong Hyun Kim, and Seok-Hee Lee, *IEEE Electron Device Letters*, 35 (12), 1182-1184 (2014)
5. "First Demonstration of Ultra-Thin SiGe-Channel Junctionless Accumulation-Mode (JAM) Bulk FinFETs on Si Substrate with PN Junction-Isolation Scheme", Dong-Hyun Kim, Tae Kyun Kim, Young Gwang Yoon, **Byeong-Woon Hwang**, Yang-Kyu Choi, Byung Jin Cho, and Seok-Hee Lee, *IEEE Journal of the Electron Devices Society*, 2 (5), 123-127 (2014)
6. "Enhanced Device Performance of Germanium Nanowire Junctionless (GeNW-JL) MOSFETs by Germanide Contact Formation with Ar Plasma Treatment", Young Gwang Yoon, Tae Kyun Kim, In-Chan Hwang, Hyun-Seung Lee, **Byeong-Woon Hwang**, Jung-Min Moon, Yu-Jin Seo, Suk Won Lee, Moon-Ho Jo, and Seok-Hee Lee, *ACS Applied Materials & Interfaces*, 6 (5), 3150-3155 (2014)
7. "First Demonstration of Junctionless Accumulation-Mode Bulk FinFETs with Robust Junction-Isolation", Tae Kyun Kim, Dong Hyun Kim, Young Gwang Yoon, Jung Min Moon, **Byeong Woon Hwang**, Dong-II Moon, Gi Seong Lee, Dong Wook Lee, Dong Eun Yoo,

Hae Chul Hwang, Jin Soo Kim, Yang-Kyu Choi, Byung Jin Cho and Seok-Hee Lee, IEEE Electron Device Letters, 34 (12), 1479-1481 (2013)

Conferences

1. "Output Enhancement of Triboelectric Energy Harvester by Micro-Porous Triboelectric Layer", Daewon Kim, Byeong-Woon Hwang, Jin-Woo Han, Myeong-Lok Seol, Yura Oh, and Yang-Kyu Choi, International Electron Devices Meeting (IEDM), Washington D.C., USA, Dec. 8, 2015
2. "Effective Ar plasma treatment for germanide contact formation of germanium nanowire junctionless(Ge-NW JL) MOSFETs", Young Gwang Yoon, Tae Kyun Kim, Hyun-Seung Lee, Inchan Hwang, **Byeong-Woon Hwang**, Jung-Min Moon, Yu-Jin Seo, Suk Won Lee, Moon-Ho Jo and Seok-Hee Lee, Materials Research Society (MRS), San Francisco, CA, USA, Apr. 03. 2013
3. "Estimation of initial surface potential and modeling of inversion charge for double-gate MOSFET", **황병운**, 이창용, 이석희, 양지운, The Korean Conference on Semiconductors, 2012. 2. 17

Patents

1. "Ultra-Thin FinFET 제조 방법 및 이를 이용하여 제조된 Ultra-Thin FinFET", **Byeong-Woon Hwang**, Woo Jin Jeong, Jung-Min Moon, Tae-Kyun Kim and Seok-Hee Lee, Feb. 20, 2014, Registered (10-1367989)

REFERENCE

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